#### GaAs Photo-Cathodes as Sources for Low-Velocity Electron Coolers

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## **Electron Coolers**





Reaction rate coefficient



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#### 20 20 20 $Fe^{17+} + e \rightarrow Fe^{16+} + \gamma$ n=18 15 Coefficient $(10^{-10} \text{ cm}^3)$ 19 2s<sup>2</sup>2p<sup>5</sup>(<sup>2</sup>P .\_)nl 6f,g,h 10 2s2p<sup>6</sup>nl Savin, ApJ 489 (1997)] 6d Recombination rates of n=610 5 15 20 25 HCI in astrophysical plasma 10... 2s2p<sup>6</sup>(<sup>2</sup>S<sub>1/2</sub>)nl n=7 Rate **Electron Cooler** 0 0 20 40 60 80 120 140 100 Center of Mass Energy (eV) $s^{-1}$ 30 (a) Experiment $(10^{-10} \text{ cm}^3 \text{ s})$ 20 10 12 coefficient 8 -n=9 l←10 |11...| 2s2p<sup>2</sup>(<sup>2</sup>P<sub>1/2</sub>)nl 10... n=89 series 10 $2s2p^{2}(^{2}P_{3/2})nl$ series Rate 0 120 140 60 80 0 20 40 100 Center of Mass Energy (eV) The Heidelberg Electron Cooler Storage Ring

TSR

[Savin, ApJ Suppl. Ser. 147 (2003)]



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#### Electron cooling of molecular (slow!) ions



- Maximum rigidity:  $r B_{max}$ for TSR:  $\approx 1.4$  Tm
- Maximum velocity:

$$v_{max} = \frac{Z_{ion}}{M_{ion}} r B_{max} \rightarrow E_{cool} \sim \frac{Z_{ion}^2}{M_{ion}^2}$$

- e.g. CHD<sup>+</sup> (15 u) :  $E_{cool} \sim 230 \text{ eV}$ D<sub>3</sub>O<sup>+</sup> (22 u) :  $E_{cool} \sim 110 \text{ eV}$ DCND<sup>+</sup>(30 u) :  $E_{cool} \sim 55 \text{ eV}$
- But:  $I_{\rm e} \sim E_{\rm cool}^{3/2}$  !

electron density **degrades** ion beam lifetime **degrades** 

• There is a **practical**  $M_{ion,max}$ 

Ion loss rate exceeds electron cooling rate ...











## Cold cooler electron source

# Standard cooler electron source: **thermionic cathode**

$$J \sim T^2 \exp\left(\frac{-\Phi}{k_B T}\right)$$



established technology high J are possible ...

high electron-T( $k_{\rm B}T > 100 \text{ meV}$ )





## Cold cooler electron source

TSR electron cooler: GaAs:(Cs/O) photocathodes

 Electrons overcome Φ by absorbtion of photons (hv > Φ)





 Negative Electron Affinity (NEA) e's can thermalise to a state close to vacuum energy.

$$T_{\rm e} \sim T_{\rm cath}$$
  
( $k_{\rm B}T \approx 10 {\rm meV}$ )







Negative Electron Affinity:



# GaAs:(Cs/O) Electron Source





#### Electron cooling at low velocity







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#### Electron cooling at low velocity







# Thank you!

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#### Photo-cathode electron cooler

#### Photocathode setup Cs/O **GaAs**-**Preparation chamber:** Cs/O activation, thermal cleaning, Sapphire spectroscopy, 4 cathodes 5.10<sup>-12</sup> mbar Magnetic manip. **E-gun Gun chamber:** LN2-coldhead, HV-supply, Laser illumination **Atomic H / Loading chamber:** TSR vacuum, 2·10<sup>-11</sup> mbar In-vacuo cleaning by H radicals, air-lock for cathode loading, 10<sup>-9</sup> mbar

#### Photo-cathode electron cooler



#### Photo-cathode electron cooler

#### Surface cleaning by H radicals

- Cathode cleaning by bakeout can be done 3-4 times. (non-volatile Ga- and As-oxides accumulate on the surface.)
  Gradual decrease of the quantum efficiency.
- Ga-oxides can be removed by

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- 1. etching in HCl solution.
  - $\rightarrow$  Requires removal of cathode from setup.  $\textcircled{\odot}$
- 20 2. Exposure to H• radicals in vacuum  $Ga_2O_3 + 4 H \rightarrow Ga_2O + 2 H_2O$ , 15  $As_2O_3 + 6 H \rightarrow 3 H_2O + As_2\left(\frac{1}{2} As_4\right)$ QE (%) 10  $\rightarrow$  Cathode can stay in vacuum.  $\bigcirc$ 5 0 0 5 10 15 20 25 30 activation cycle



[Orlov, J. Appl. Phys. 106 (2009)]